## AMENDMENTS TO THE CLAIMS

- (Currently Amended) A method comprising:
   placing a substrate with a ferroelectric polymer layer formed thereon in a chamber; and
   sputtering a metal layer at a reduced flux on the ferroelectric polymer layer in the
   presence of a flux reducer.
- 2. (Currently Amended) The method of Claim 1, wherein sputtering the flux reducer comprises sputtering in the presence of a collimator.
- 3. (Currently Amended) The method of Claim 2, wherein sputtering may be performed comprises sputtering at a pressure less than approximately 10 milliTorr.
- 4. (Currently Amended) The method of Claim 32, wherein sputtering may be performed comprises sputtering at a pressure equal to or less than approximately 2.5 milliToπ.
- (Original) The method of Claim 1, wherein sputtering comprises:
  forming a metal layer of at least one of TiN, TaN, TiNSi, and TaNSi.
- (Original) The method of Claim 1, wherein sputtering comprises:
  sputtering with an ion gun.
- 7. (Original) A method comprising: placing a substrate with a ferroelectric polymer layer formed thereon in a chamber; and forming an intermetallic layer between a metal layer and the ferroelectric polymer layer.
- (Original) The method of Claim 7, wherein forming comprises:
  sputtering with an ion gun.
- (Original) The method of Claim 7, wherein forming comprises: forming a layer of at least one of TiN, TaN, TiNSi, and TaNSi.

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- (Original) The method of Claim 7, further comprising:
  amorphizing the intermetallic layer.
- (Original) The method of Claim 10, wherein amorphizing comprises:
  implanting ions within the intermetallic layer.
- (Original) The method of Claim 11, wherein implanting comprises:
  implanting at least one of Si ions, Ge ions, and any of the inert gas ions in the intermetallic layer.
- 13. (Original) The method of Claim 10, wherein amorphizing comprises: forming the intermetallic layer with a technique that renders the intermetallic layer amorphous.
- 14. (Original) The method of Claim 13, wherein forming comprises: forming the intermetallic layer with a chemical vapor deposition process.

15-24 (Canceled)